

isc N-Channel MOSFET Transistor

2SK1444

DESCRIPTION

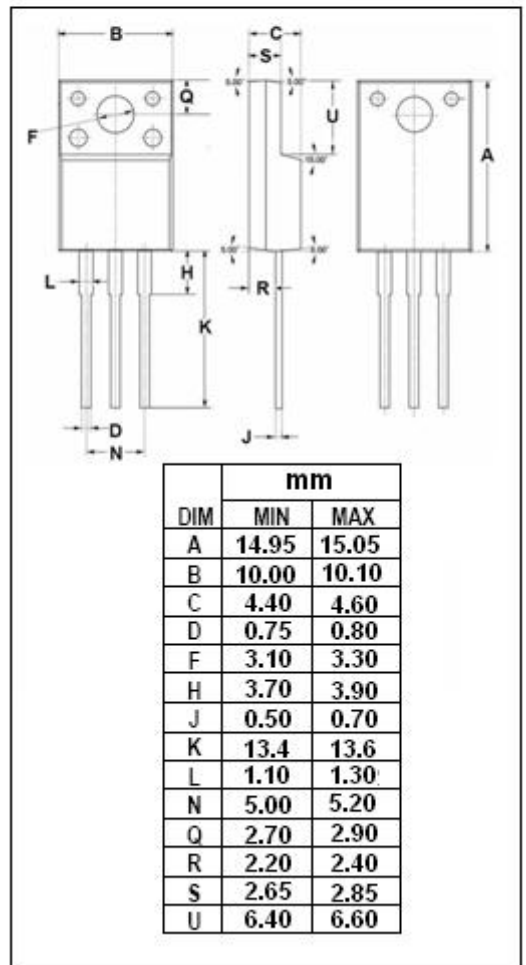
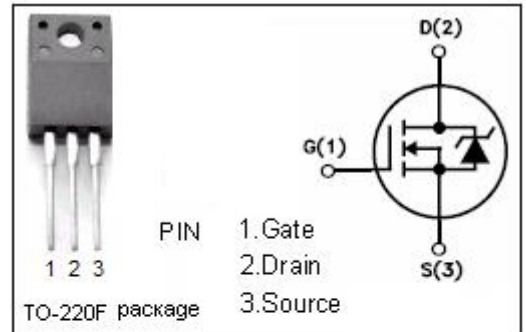
- Drain Current  $-I_D=3A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}= 450V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

- Designed for high voltage, high speed power switching

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	ARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	450	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $T_C=25^\circ C$	3	A
$P_{tot}$	Total Dissipation@ $T_C=25^\circ C$	25	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc N-Channel Mosfet Transistor****2SK1444****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 1mA	450			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =10 V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.0		3.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =0.5A		2.0	2.6	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0			± 100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =450V; V <sub>GS</sub> = 0			1	mA
V <sub>SD</sub>	Diode Forward Voltage	I <sub>F</sub> =3A; V <sub>GS</sub> =0			1.8	V
t <sub>r</sub>	Rise time	V <sub>GS</sub> =10V; I <sub>D</sub> =1.5A; R <sub>L</sub> =50 Ω		20		ns
t <sub>on</sub>	Turn-on time			32		ns
t <sub>f</sub>	Fall time			35		ns
t <sub>off</sub>	Turn-off time			115		ns